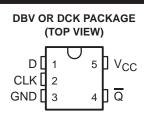
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- EPIC<sup>™</sup> (Enhanced-Performance Implanted CMOS) Submicron Process
- I<sub>off</sub> Feature Supports Partial-Power-Down Mode Operation
- Supports 5-V V<sub>CC</sub> Operation
- Package Options Include Plastic Small-Outline Transistor (DBV, DCK) Packages

### description



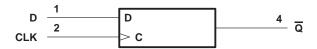
This single positive-edge-triggered D-type flip-flop is designed for 1.65-V to 5.5-V  $V_{CC}$  operation.

When data at the data (D) input meets the setup time requirement, the data is transferred to the  $\overline{Q}$  output on the positive-going edge of the clock pulse. Clock triggering occurs at a voltage level and is not directly related to the rise time of the clock pulse. Following the hold-time interval, data at the D input can be changed without affecting the levels at the outputs.

The SN74LVC1G80 is characterized for operation from -40°C to 85°C.

FUNCTION TABLE								
INPU	JTS	OUTPUT						
CLK	D	Q						
$\uparrow$	Н	L						
$\uparrow$	L	н						
L	Х	Q <sub>0</sub>						

### logic symbol<sup>†</sup>



<sup>†</sup> This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.



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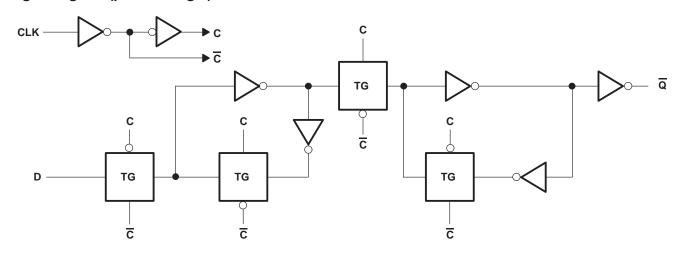
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## logic diagram (positive logic)



### absolute maximum ratings over operating free-air temperature range (unless otherwise noted)<sup>†</sup>

Input vo Output v Input cla Output o Continu Continu Package		$\begin{array}{c} -0.5 \text{ V to } 6.5 \text{ V} \\ -0.5 \text{ V to } V_{CC} + 0.5 \text{ V} \\ -50 \text{ mA} \\ -50 \text{ mA} \\ \pm 50 \text{ mA} \\ \pm 100 \text{ mA} \\ 347^{\circ}\text{C/W} \\ 389^{\circ}\text{C/W} \end{array}$
Storage	temperature range, T <sub>stg</sub>	

<sup>†</sup> Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input negative-voltage and output voltage ratings may be exceeded if the input and output current ratings are observed.

2. The value of  $V_{CC}$  is provided in the recommended operating conditions table.

3. The package thermal impedance is calculated in accordance with JESD 51.



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### recommended operating conditions (see Note 4)

			MIN	MAX	UNI		
	Currhuseltere	Operating	1.65	5.5	V		
Vcc	Supply voltage	Data retention only	1.5				
		V <sub>CC</sub> = 1.65 V to 1.95 V	$0.65 \times V_{CC}$				
		$V_{CC} = 2.3 V \text{ to } 2.7 V$	1.7		V		
VIH	High-level input voltage	$V_{CC} = 3 V \text{ to } 3.6 V$	2		v		
		$V_{CC} = 4.5 \text{ V} \text{ to } 5.5 \text{ V}$	$0.7 \times V_{CC}$	$ \begin{array}{c} 2 \\ \hline 0.35 \times V_{CC} \\ 0.7 \\ 0.8 \\ 0.3 \times V_{CC} \\ 0 \\ 5.5 \\ 0 \\ V_{CC} \\ -4 \\ -8 \\ -16 \\ -24 \\ \end{array} $			
		V <sub>CC</sub> = 1.65 V to 1.95 V		$0.35 \times V_{CC}$			
VIL							
	Low-level input voltage	$V_{CC} = 3 V \text{ to } 3.6 V$		0.8	V		
		$V_{CC} = 4.5 V \text{ to } 5.5 V$		$0.3 \times V_{CC}$			
VI	Input voltage	·	0	5.5	V		
Vo	Output voltage		0	VCC	V		
	High-level output current	V <sub>CC</sub> = 1.65 V		-4			
		V <sub>CC</sub> = 2.3 V		-8			
ЮН				-16	mA		
		VCC = 3 V		-24			
		$V_{CC} = 4.5 V$		-32			
		V <sub>CC</sub> = 1.65 V		4			
	Low-level output current	V <sub>CC</sub> = 2.3 V		8			
IOL		N 2)/		16	mA		
		$V_{CC} = 3 V$		24			
		$V_{CC} = 4.5 V$		32			
	Input transition rise or fall rate	$V_{CC}$ = 1.8 V ± 0.15 V, 2.5 V ± 0.2 V					
$\Delta t / \Delta v$		$V_{CC} = 3.3 V \pm 0.3 V$		10	ns/V		
		$V_{CC} = 5 V \pm 0.5 V$		5			
TA	Operating free-air temperature	·	-40	85	°C		

NOTE 4: All unused inputs of the device must be held at V<sub>CC</sub> or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.



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PARAMETER	TEST CONDITIONS	Vcc	MIN	TYPŤ	MAX	UNIT
	I <sub>OH</sub> = -100 μA	1.65 V to 5.5 V	V <sub>CC</sub> -0.1			
	$I_{OH} = -4 \text{ mA}$	1.65 V	1.2			
	$I_{OH} = -8 \text{ mA}$	2.3 V	1.9			.,
VOH	$I_{OH} = -16 \text{ mA}$		2.4			V
	I <sub>OH</sub> = -24 mA	3 V	2.3			
	I <sub>OH</sub> = -32 mA	4.5 V	3.8			
	I <sub>OL</sub> = 100 μA	1.65 V to 5.5 V			0.1	
	I <sub>OL</sub> = 4 mA	1.65 V			0.45	
	I <sub>OL</sub> = 8 mA	2.3 V			0.3	
VOL	I <sub>OL</sub> = 16 mA				0.4	V
	I <sub>OL</sub> = 24 mA	3 V			0.55	
	I <sub>OL</sub> = 32 mA	4.5 V			0.55	
II D input	V <sub>I</sub> = 5.5 V or GND	0 to 5.5 V			±10	μA
loff	$V_{I} \text{ or } V_{O} = 5.5 \text{ V}$	0			±10	μΑ
ICC	$V_{I} = 5.5 \text{ V or GND}, \qquad I_{O} = 0$	1.65 V to 5.5 V			20	μΑ
ΔICC	One input at $V_{CC}$ – 0.6 V, Other inputs at $V_{CC}$ or GND	3 V to 5.5 V			500	μA
Ci	V <sub>I</sub> = V <sub>CC</sub> or GND	0				pF

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

<sup>†</sup> All typical values are at  $V_{CC} = 3.3 \text{ V}$ ,  $T_A = 25^{\circ}\text{C}$ .

# timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 through 4)

				V <sub>CC</sub> = 1.8 V         V <sub>CC</sub> = 2.5 V           ± 0.15 V         ± 0.2 V		V <sub>CC</sub> = 3.3 V ± 0.3 V		V <sub>CC</sub> = 5.5 V ± 0.5 V		UNIT	
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
fclock	Clock frequency										MHz
tw	Pulse duration, CLK high or low										ns
		Data high									
t <sub>su</sub>	Setup time before CLK↑ Data low										ns
t <sub>h</sub>	Hold time, data after $CLK^\uparrow$										ns

## switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 through 4)

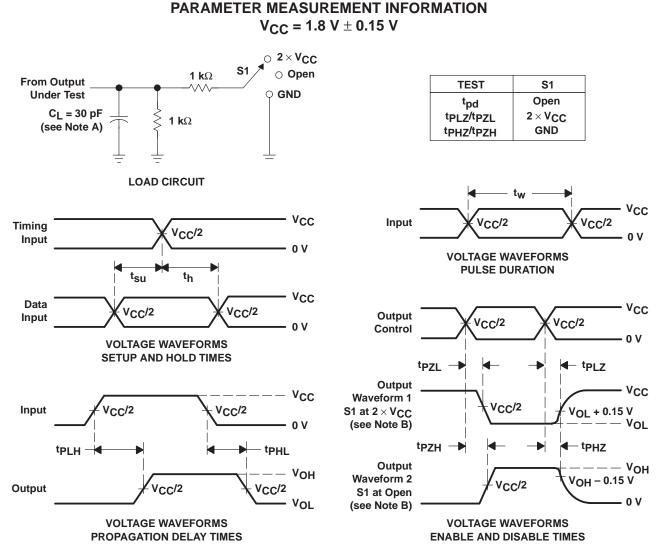
PARAMETER	FROM (INPUT)	TO (OUTPUT)	V <sub>CC</sub> = ± 0.1		V <sub>CC</sub> = ± 0.2		= ۷ <sub>CC</sub> ± 0.3		= V <sub>CC</sub> ± 0.		UNIT	
		(001101)	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX		
f <sub>max</sub>											MHz	
<sup>t</sup> pd	CLK	Q									ns	

### operating characteristics, $T_A = 25^{\circ}C$

	PARAMETER	TEST CONDITIONS	V <sub>CC</sub> = 1.8 V	V <sub>CC</sub> = 2.5 V	V <sub>CC</sub> = 3.3 V	V <sub>CC</sub> = 5 V	UNIT
	FARAMETER	TEST CONDITIONS	TYP	TYP	TYP	TYP	UNIT
Cpd	Power dissipation capacitance	f = 10 MHz					pF



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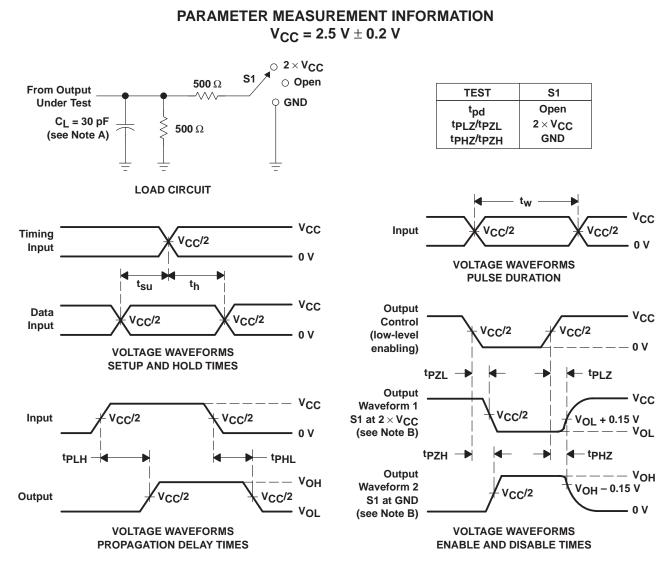
- NOTES: A. CI includes probe and jig capacitance.
  - B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control. C. All input pulses are supplied by generators having the following characteristics: PRR  $\leq$  10 MHz, Z<sub>O</sub> = 50  $\Omega$ , t<sub>f</sub>  $\leq$  2 ns, t<sub>f</sub>  $\leq$  2 ns.
  - D. The outputs are measured one at a time with one transition per measurement.

  - E. tpLz and tpHz are the same as tdis.
  - F. tpzL and tpzH are the same as ten.
  - G. tpl H and tpHI are the same as tpd.

### Figure 1. Load Circuit and Voltage Waveforms



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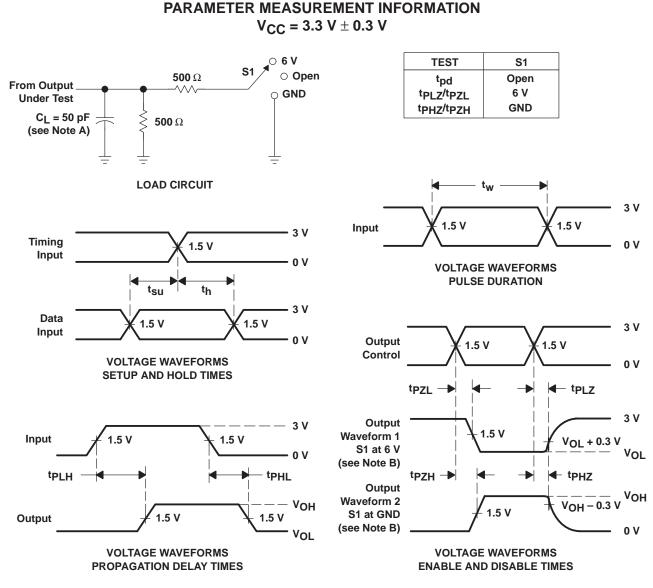
NOTES: A. CL includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
   C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z<sub>Q</sub> = 50 Ω, t<sub>f</sub> ≤ 2 ns, t<sub>f</sub> ≤ 2 ns.
- D. The outputs are measured one at a time with one transition per measurement.
- E.  $t_{PLZ}$  and  $t_{PHZ}$  are the same as  $t_{dis}$ .
- F.  $t_{PZL}$  and  $t_{PZH}$  are the same as  $t_{en}$ .
- G.  $t_{PLH}$  and  $t_{PHL}$  are the same as  $t_{pd}$ .

### Figure 2. Load Circuit and Voltage Waveforms



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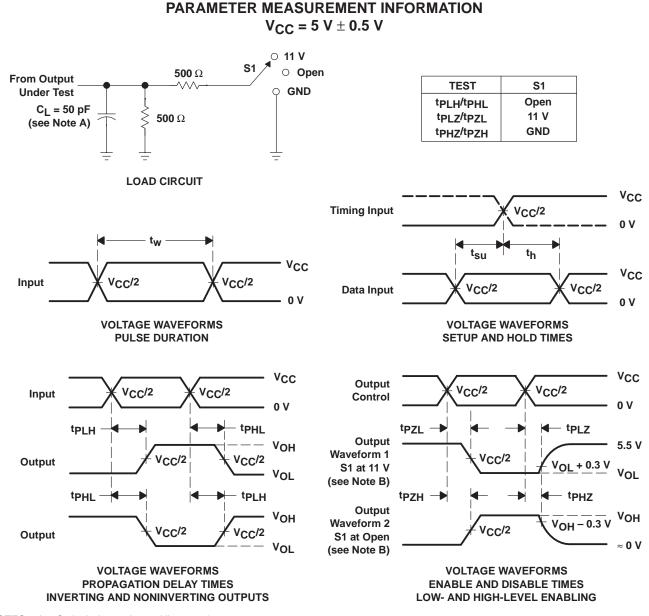


- NOTES: A. CL includes probe and jig capacitance.
  - B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
  - C. All input pulses are supplied by generators having the following characteristics: PRR  $\leq$  10 MHz, Z<sub>O</sub> = 50  $\Omega$ , t<sub>f</sub>  $\leq$  2.5 ns, t<sub>f</sub>  $\leq$  2.5 ns.
  - D. The outputs are measured one at a time with one transition per measurement.
  - E.  $t_{PLZ}$  and  $t_{PHZ}$  are the same as  $t_{dis}$ .
  - F.  $t_{PZL}$  and  $t_{PZH}$  are the same as  $t_{en}$ .
  - G. tPLH and tPHL are the same as tpd.

### Figure 3. Load Circuit and Voltage Waveforms



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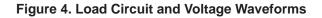


NOTES: A. CL includes probe and jig capacitance.

B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z<sub>O</sub> = 50 Ω, t<sub>f</sub> ≤ 2.5 ns, t<sub>f</sub> ≤ 2.5 ns.

D. The outputs are measured one at a time with one transition per measurement.

- E.  $t_{PLZ}$  and  $t_{PHZ}$  are the same as  $t_{dis}$ .
- F.  $t_{P7I}$  and  $t_{P7H}$  are the same as  $t_{en}$ .
- G. tPLH and tPHL are the same as tpd.





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